Index

a

Abbe limit 163
adhesion weak method 195
ammonium perrhenate 46
angle/angular-resolved photoemission spectroscopy (ARPES) 126, 146, 147
antimonene 7
atmospheric pressure chemical vapor deposition (APCVD) 40
  graphene 42
  low-pressure chemical vapor deposition 48–53
  multi-element materials 48
  single-element materials 40–42
  TMDCs bi-element materials 42–47
atomic layer deposition (ALD) 18, 201, 299
auxiliary glue compound 89

b

band alignment 47, 99, 104, 105, 111, 112, 126–129, 142, 144, 147, 159, 169, 172, 175, 211, 212, 223, 228, 231–233, 296, 300
battery 271
  lithium-ion battery 273
  supercapacitors 276–277
bilayer graphene 133–135, 139, 140, 145, 147, 164, 165
biosensors 12, 282–284
bismuthene 7
black phosphorus (BP) 6, 269
  capsulated by hBN 141–142
Boltzmann equation 141
boron nitride (BN) 90
borophene 7, 8

c

carbon fiber cloth (CFC) 114
carbon sublattices 14
catalyst 12, 41, 47, 111, 112, 268, 269, 277–282
charge transfer 50, 57, 98, 107, 111, 126–129, 142, 157, 159, 175, 229, 234, 243, 271, 272, 277, 283, 299, 303
chemical etching 70, 72, 74, 279, 281
chemical sensors 102–104
chemical vapor deposition (CVD) method 3, 7, 9, 17–18, 38–52, 54, 56–57, 69–71, 78, 82, 86, 88, 99, 101, 105, 108, 115, 131, 177, 188, 197, 228, 264, 275, 277, 297, 301, 304, 307
conduct band minimum (CBM) 135, 268, 269
contact resistance 112, 171, 190, 192–195, 200, 208, 304, 307, 308
continuum Dirac model 135

Van der Waals Heterostructures: Fabrications, Properties, and Applications, First Edition.
Edited by Zheng Zhang, Zhuo Kang, Qingliang Liao, and Yue Zhang.

controllable synthesis
of 2D-1D heterostructures 82–84
of 2D-2D heterostructures 76–82
of 2D-3D heterostructures 85–86
Coulomb interaction 15, 37, 135, 172, 175, 200, 239

d

dark field optical microscopy 91
density functional theory (DFT) 11, 45–47, 50, 126, 127, 129, 135, 141, 169, 173, 268, 280
dimethyl sulfide (DES) 60
direct bandgap 1, 5, 7, 8, 11, 46, 47, 60, 108, 110, 167, 173, 206, 236, 239
direct growth method 99, 100
doping's intrinsic 126
dry transfer method
pick-up 89–92
stamps 88–89
thermal-release tape 86–88

e

electric-field integrated STM-STS technique 159–160
electrochemical delamination methods 72–74
electrochemical reaction 72, 270, 274, 275
electrostatic force microscopy (EFM) 145
encapsulator 137
energy dispersive spectroscopy (EDS) mode 161, 162
exciton diffusion length (L_E) 175
exfoliated 2D materials 34
liquid 35–37
mechanical 34–36
exfoliation 6, 7, 9, 17–18, 33–37, 90, 114, 195, 297, 301, 310
exhaust gas treatment system 58
external gate voltage 169, 170

f

face centered cubic (FCC) 14, 17
Fermi level 15, 107, 108, 111, 127, 132, 137, 138, 159, 170, 176, 177, 188, 190, 193, 195, 212, 234, 243, 280, 304
field-effect transistor (FET) 82, 101–102, 197
advantages characteristics 199
basic structure 198–199
dielectric materials 199–201

g

gas transportation system 58
gateway 173
germanene 6
Goodenough–Kanamori–Anderson rules 131
graphene processes 247, 284
bilayer graphene 133–135, 139, 140, 145, 147, 164, 165
planar graphene 33
graphite-diacetylene 5, 6
guided tissue regeneration (GTR) membrane 285

h

half integer quantum Hall effect (HIQHE) 139
Hall effect 6, 125, 130, 138, 139
Hall mobility 52, 141
hexaethynylbenzene 5
hexagonal boron nitride (h-BN) 3, 8–9, 45, 56, 90, 92, 137–138
black phosphorus (BP) capsulated by 141–142
graphene capsulated by 138–140
transition metal dichalcogenides capsulated by 140
with honeycomb lattice 137
high-angle annular dark-field (HAADF) detector 142, 143

highly ordered pyrolytic graphite (HOPG) 86, 130
horizontal 2D-2D heterostructures 79–80
Hubbard model 135
hydrogen energy 267
  by water electrolysis 270–271
  by water photolysis 268–270
hydrogen evolution reaction 12, 36, 37, 112, 271
hydrogen gas 40, 48, 49, 112

i
indirect band gaps 1, 8, 11, 46, 110, 167, 173, 239
integer quantum Hall effect (IQHE) 136, 138, 139, 141
ion intercalation 35, 37
Ising model 129

j
junction FET (JFET) 201
  applications 205–208
  current-voltage features 202–203
  device structure 205
  working principle 203–204

k
Kelvin probe force microscopy (KPFM) 145, 160, 162–163

l
laser 3, 18, 78, 80, 81, 110, 126, 166, 195, 242–245, 269
Laudau level (LL) 139
light absorption spectrum 50
light emission 110, 172
  light-emitting diode 236–242
liquid exfoliation 7, 297
  of 2D materials 35–37
liquid-precursor CVD method (LCVD) 177
lithium-ion batteries (LIBs) 112–114, 273–277
lithium ion battery 273
low-pressure chemical vapor deposition (LPCVD)
  multi-element materials 51–53
  single-element materials 48–49
  TMDCs bi-element materials 49–50

m
magnetic coupling 126, 129–134
magnetic proximity effect 133
magnetic/magneto tunneling junction (MTJ) 132, 134, 212
massless Dirac fermions 138
mechanical exfoliation 9
  Au-assisted 35
  of 2D materials 34–36
melamine 42
metal etching method 70
metal foil 69, 71
metal organic chemical vapor deposition (MOCVD) 39
  overview 57–59
  III–V group semiconductor by 59–60
  TMDCs by 60–63
methane gas 40, 42
microelectronic devices 188
micromechanical exfoliation 17
microwave (MW) plasma 53
mixed-dimensional VdWHs
  categorization of 97–99
  chemical sensors 102–104
  direct growth of 100–101
  transfer-assisted assembly of 99–100
  transistors and spintronics 101–102
modified element reactor (MER) 76
modulated-elemental-reactant (MER) method 76
Moiré excitons 135–136

Moiré lattice
  band structure in 134–135
  bilayer graphene in 135
  excitons 135–136
  topological 136–137
Moiré pattern 49, 134–137, 140, 142–145, 160, 161, 163, 166
molecular beam epitaxy (MBE) 6, 7, 18, 82, 137
molecular evaporator deposition 5
molybdenum disulfide 56, 86, 191, 194–196
Moore's Law 207, 301, 305, 306
MoS_2/GaN 85, 268
Mott metal-insulator transition 135
multi-element materials
  atmospheric pressure chemical vapor deposition (APCVD) 48
  low-pressure chemical vapor deposition (LPCVD) 51, 53–57
multi-field microscopy techniques 158
  electric-field integrated STM-STS technique 159–160
  optical-field integrated KPFM technique 162–163
  TEM technique 161–162
  thermal-field integrated STM-STS technique 160–161
multi-field optical spectroscopy technique 163
  S-SNOM 165–166
  TERS technique and Raman spectroscopy 163–165
MXene 12, 13, 275, 276

n

nanomaterials 37, 45, 75, 99, 102, 105, 107, 111, 112, 114, 276, 282, 283, 285

o

Ohmic contact 47, 192, 193, 195, 205, 267, 304
one-dimension heterostructures 80–82
optical and vibrational spectroscopy 145–147
optical-field integrated KPFM technique 162–163
optoelectronic applications 5, 7, 34, 83, 104–110, 175
optoelectronic device system 306, 309

p

Peakforce TappingTM mode 144
phase engineering 51, 171, 194, 277–279
phosphorene 176, 177, 269, 270
photocatalytic water splitting 111–112
photodetector(s) 82, 223
  improvement strategies 234–236
  light emission
    laser 242–243
    light-emitting diode 236–242
    single photon 244–245
  optical modulators 245–247
    all-optical modulators 245–246
    electro-optic modulators 246–247
    thermo-optic modulators 247
  photoconductive effect 229–231
  photo-thermoelectric effect 233–234
  photovoltaic effect 228–229
  tunneling effect 231–232
photoelectric conversion 162, 263, 264
photogating effect 104, 170, 230, 235
photoluminescence spectroscopy (PL) 7, 9, 45, 49, 50, 51, 85, 106, 126, 127, 145, 146, 167, 168, 170, 173–177, 238, 240, 241, 245, 283, 284, 298, 299
photonic applications 104–111
photoresponse enhancement 104
pick-up methods 89–92
planar graphene 33
plasma enhanced chemical vapor deposition (PECVD)
  graphene 54–56
  overview 53–54
  TMDCs 56–57
  VG nanosheets 56
plasmon resonance frequency 105
PMMA/PVA 72
polydimethylsiloxane (PDMS) 74, 75, 88–91, 195, 197, 300

polymethyl methacrylate (PMMA) 42, 70–74, 86, 88, 89, 195, 300
polypropylene carbonate (PPC) 89–90, 197
polyvinyl alcohol (PVA) 72, 89, 276, 285
polyvinylpyrrolidone (PVP) 35
power conversion efficiency (PCE) 108, 229, 267
power-efficient electro-optic modulators 246
pseudo-Van der Waals growth method 60
pulsed laser deposition (PLD) 18

q
qPlus technique 144
quantum electrodynamics 138
quantum light-emitting 108

r
radio frequency (RF) plasma 53, 192
Raman scattering 146, 177
Raman spectroscopy 50, 85, 130, 132, 146, 158, 163, 297, 299
rechargeable batteries 112–114, 273
reflective magnetic circular dichroism (RMCD) 132

s
scanning magneto-optic Kerr microscopy 130
scanning photocurrent microscope (SPCM) 165
scanning probe microscopy 142, 144–145
scanning transmission electron microscope (STEM) 47, 48, 52, 142–143, 161, 281, 285
scanning tunneling spectroscopy (STS) 126, 135, 144, 145, 159–161
scattering-type scanning near-field optical microscope (s-SNOM) 165–166
Schottky barrier 37, 107, 171, 193–196, 201, 208, 233, 241
Schottky diodes 47, 192
Schottky junction 105, 106, 108, 109, 111, 112, 192, 193, 196, 213
selenium powder 42, 43
semiconducting 2D materials 34
short-wave infrared (SWIR) 104
single-element materials
  atmospheric pressure chemical vapor deposition (APCVD) 40–48
  low-pressure chemical vapor deposition (LPCVD) 48–53
single photon 108, 173, 244–245
single quantum emitters (SQEs) 244, 245
SiO_2/Si substrate 4, 9, 44, 45, 56, 70, 71, 74, 75, 82, 86, 92, 108, 139
sodium-ion batteries (SIBs) 113, 114, 273–277
soft-chemical method 131
solar energy 111, 173, 261–267, 269
solvothermal 18, 99, 114, 276–278, 280
spintronics 101–102, 134
stacking fault phases 14
stamps 88–89
STEM-ADF 52
strain-engineered optical properties 173–175
strain-induced bandgap transition 167
strain-induced piezopotential 175
substrate etching techniques 69–72
supercapacitors 111, 113–115, 273, 276, 277, 284

t
thermal emission equations 171
thermal-field integrated STM-STS technique 160–161
thermal-release tape 86–88
thermo-optic modulators 247
III–V group semiconductor 59–60
3D material systems 295
time-dependent density functional theory-molecular dynamics (TDDFT-MD) 129
time-domain density functional (TDDFT) method 129

tissue engineering 282–285
transfer-assisted assembly 99–100
transistors 101–102
  field-effect transistor 197–212
  and spintronics 101–102
transition metal carbides (TMCs) 12–15
transition metal dichalcogenides (TMDCs) 9, 12
  bi-element materials
    atmospheric pressure chemical vapor deposition (APCVD) 40–48
    low-pressure chemical vapor deposition (LPCVD) 48, 49
  capsulated by hBN 140
  by MOCVD 60–63
  by PECVD 56–57
transition metal oxides (TMOs) 15–18, 275, 284
transmission electron microscopy (TEM) 49, 50, 77, 78, 81, 83, 84, 142–143, 158, 161–162, 166, 196, 270, 278, 281, 297
tungsten 48, 56, 62
tunneling conductance 159
tunneling current 46, 132, 144, 159, 190, 210–212, 231
tunneling FET (TFET) 208
  applications 211–212
  history 208–209
  mechanism 209–211
tunneling magnetoresistance 134
twisted bilayer graphene (TBG) 134, 135, 164, 165
2D-0D hybridization 104–105
2D-1D hybridization 105–108
2D-2D heterostructures
  horizontal 79–80
  vertical 76–79
2D-3D hybridization 108–110
2D layered materials (2DLMs) 295–296
  classification 3
  elemental 3
  V group A 6–7
  IV A group 3–6
  hexagonal boron nitride (h-BN) 8–9
  industry-compatible integration process 299–301
  mass production 297
  metrology 297–299
  silicon technology 301–307
    compatibility 301–307
  III A group 7–8
  transition metal carbides (TMCs) 12–14
  transition metal dichalcogenides (TMDCs) 9–12
  transition metal oxides (TMOs) 15–18
2D Van der Waals structures
  electrical properties 167–169
    electric field-engineered 169–170
    strain-engineered 167–169
    thermal-engineered 171–172
  multi-field coupling effect characterization for 158–166
  multi-field integration characterization 166
  multi-field microscopy technique 158–163
  multi-field optical spectroscopy technique 163–166
  optical properties 172–177
    electrical-engineered 175–177
    strain-engineered 173–175
    thermal-engineered 177

u

ultrasonication 35–37
  assisted liquid exfoliation 37

v

vacuum annealing 70
valence band maximum (VBM) 135, 228, 268, 269
valleytronics 132–134
Van der Waals (VdW)
  integration 213–216
  heterojunctions 187–188
Van der Waals heterostructures (vdWHs) 2, 223
  band alignment in 126–129

characterization techniques
for 142–147
charge transfer in 126–129
field-effect transistor 197–201
junction field-effect
transistor 201–208
magnetic coupling in 129–134
metal-semiconductor
junctions 192–197
Moiré pattern 134–137
PN junctions 188–192
for protection 137–142
roadmap 307–308
spintronics in 134
tunneling field-effect
transistor 208–212
valleytronics in 132–134
vertical 2D-2D heterostructures 76–77
VG nanosheets 56

w
water film 74, 75
wedging transfer method 74–75
wet transfer 69
electrochemical delamination
methods 72–74
substrate etching techniques 69–72
wedging transfer methods 74–75
white graphene 8

x
XPS 50, 278

y
Young's modulus 4

z
Zeeman splitting 132, 133